

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5051-531DV		Serial No. To Be Assigned	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Zhibo Zhang			
				Filing Date: To Be Assigned		GAU:	
U.S. PATENT DOCUMENTS							
Examiner Initials	Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate	
dlh	1	6,420,751	07/16/2002	Maeda et al.	257	302	
	2	6,049,106	04/11/00	Forbes	257	329	
	3	5,739,057	04/14/98	Tiwari et al.	438	172	
	4	5,757,038	05/26/98	Tiwari et al.	257	192	
dlh	5	5,106,778	04/21/92	Hollis et al.	437	90	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
dlh	6	Yeo et al., <i>Nanoscale Ultra-Thin-Body Silicon-on-Insulator P-MOSFET With a SiGe/Si Heterostructure Channel</i> , IEEE Electron Device Letters, Vol. 21, No. 4, April 2000, pp. 161-163					
	7	<i>International Technology Roadmap for Semiconductors, 1999 Edition</i>					
	8	Lee et al., <i>Super Self-Aligned Double-Gate (SSDG) MOSFETs Utilizing Oxidation Rate Difference and Selective Epitaxy</i> , International Electron Devices Meeting, 1999, pp. 71-74					
	9	Hergenrother et al., <i>The Vertical Replacement-Gate (VRG) MOSFET: A 50-nm Vertical MOSFET With Lithography-Independent Gate Length</i> , International Electron Devices Meeting, 1999, pp. 75-78					
	10	Yang et al., <i>25-nm p-Channel Vertical MOSFET's With SiGeC Source-Drains</i> , IEEE Electron Device Letters, Vol. 20, No. 6, June 1999, pp. 301-303					
	11	Subramanian et al., <i>Low-Leakage Germanium-Seeded Laterally-Crystallized Single-Gran 100-nm TFT's for Vertical Integration Applications</i> , IEEE Electron Device Letters, Vol. 20, NO. 7, July 1999, pp. 341-343					
	12	Choi et al., <i>Ultra-Thin Body SOI MOSFET for Deep-Sub-Tenth Micro Era</i> , International Electron Devices Meeting, 1999, pp. 919-921					
	13	Wong, <i>Vertical Slab</i> , IEDM Short Course, 1999, p. 30					
	14	Jin et al., <i>Nickel Induced Crystallization of Amorphous Silicon Thin Films</i> , Journal of Applied Physics, Vol. 84, No. 1, July 1, 1998, pp. 194-200					
	15	Hisamoto et al., <i>A Folded-Channel MOSFET for Deep-Sub Tenth Micron Era</i> , International Electron Devices Meeting, 1998, pp. 1032-1034					
	16	Wong et al., <i>Device Design Considerations for Double-Gate, Ground-Plane, and Single-Gated Ultra-Thin SOI MOSFET's at the 25 nm Channel Length Generation</i> , International Electron Devices Meeting, 1998, pp. 407-410					
	17	Yu et al., <i>"Ultra-Thin-Body Silicon-on-Insulator MOSFET's for Terabit-Scale Integration"</i> ; 1997 International Semiconductor Device Research Symposium, University of Virginia, Charlottesville, VA, Dec. 11-13, 1997, p. 623					
	18	Leobandung et al., <i>Wire-Channel and Wrap-Around-Gate Metal-Oxide-Semiconductor Field-Effect Transistors With a Significant Reduction of Short Channel Effects</i> , J. Vac. Sci. Technol. B, Vol. 5, No. 6, Nov/Dec 1997, pp. 2791-2794					
	19	Taur et al., <i>CMOS Scaling Into the Nanometer Regime</i> , Proceedings of the IEEE, Vol. 85, No. 4, April 1997, pp. 486-504					
	20	Auth et al., <i>Scaling Theory for Cylindrical Fully-Depleted, Surrounding-Gate MOSFET's</i> , IEEE Electron Device Letters, Vol. 18, No. 2, February 1997, pp. 74-76					
	21	Risch et al., <i>Vertical MOS Transistors With 70 nm Channel Length</i> , IEEE Transactions on Electron Devices, Vol. 43, No. 9, September 1996, pp. 1495-1498					
	22	Wann et al., <i>A Comparative Study of Advanced MOSFET Concepts</i> , IEEE Transactions on Electron Devices, Vol. 43, No. 10, October 1996, pp. 1742-1753					
	23	Tanaka et al., <i>Ultrafast Operation of V_{th}-Adjusted p^+-n^+ Double-Gate SOI MOSFET's</i> , IEEE Electron Device Letters, Vol. 15, No. 10, October 1994, pp. 386-388					
	24	Colinge et al., <i>Silicon-on-Insulator "Gate-All-Around Device"</i> , International Electron Devices Meeting, 1990, pp. 595-598					
dlh	25	Takato et al., <i>High Performance CMOS Surrounding Gate Transistor (SGT) for Ultra High Density LSIs</i> , International Electron Devices Meeting, 1988, pp. 222-225					

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